

# Sensitive SCRs

(0.8 A to 10 A)

## General Description

The Teccor line of sensitive SCR semiconductors are half-wave unidirectional, gate-controlled rectifiers (SCR-thyristor) which complement Teccor's line of power SCRs. This group of packages offers ratings of 0.8 A to 10 A, and 200 V to 600 V with gate sensitivities of 12  $\mu$ A to 500  $\mu$ A. For gate currents in the 10 mA to 50 mA ranges, see "SCRs" section of this catalog.

The TO-220 and TO-92 are electrically isolated where the case or tab is internally isolated to allow the use of low-cost assembly and convenient packaging techniques.

Teccor's line of SCRs features glass-passivated junctions to ensure long-term device reliability and parameter stability. Teccor's glass offers a rugged, reliable barrier against junction contamination.

Tape-and-reel packaging is available for the TO-92 package. Consult the factory for more information.

Variations of devices covered in this data sheet are available for custom design applications. Consult the factory for more information.

## Features

- Electrically-isolated TO-220 package
- High voltage capability — up to 600 V
- High surge capability — up to 100 A
- Glass-passivated chip

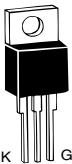
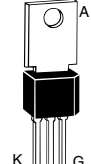
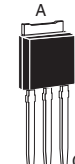
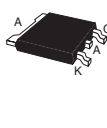
## Compak Features

- Surface mount package — 0.8 A series
- New small-profile three-leaded Compak package
- Four gate sensitivities available
- Packaged in embossed carrier tape with 2,500 devices per reel
- Can replace SOT-223

See "General Notes" on page E5 - 4 and "Electrical Specifications Notes" on page E5 - 5

V <sub>GT</sub>			I <sub>H</sub>	I <sub>GM</sub>	V <sub>GRM</sub>	P <sub>GM</sub>	P <sub>G(AV)</sub>	I <sub>TSM</sub>	dv/dt		di/dt	t <sub>gt</sub>	t <sub>q</sub>	I <sup>2</sup> t
(4) (12) (22)			(5) (15) (16) (19)	(17)		(17)		(6) (7) (13)				(8)	(9)	
Volts			mAmps	Amps	Volts	Watts	Watts	Amps	Volts/μSec		Amps/μSec	μSec	μSec	Amps <sup>2</sup> /Sec
T <sub>C</sub> or T <sub>L</sub> = -40 °C	T <sub>C</sub> or T <sub>L</sub> = 25 °C	T <sub>C</sub> or T <sub>L</sub> = 110 °C						60/50 Hz						
MAX			MAX		MIN				MIN	TYP (23)		TYP	MAX	
1.2	0.8	0.2	5	1	5	1	0.1	20/16	20		50	2	60	1.6
1.2	0.8	0.2	5	1	5	1	0.1	20/16	20		50	2	60	1.6
1.2	0.8	0.2	5	1	5	1	0.1	20/16	10		50	2	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	25		50	3	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	25		50	3	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	10		50	3	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	30		50	4	50	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	30		50	4	50	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	15		50	4	50	1.6
1.2	0.8	0.25	8	1	5	1	0.1	20/16	40		50	5	45	1.6
1.2	0.8	0.25	8	1	5	1	0.1	20/16	40		50	5	45	1.6
1.2	0.8	0.25	8	1	5	1	0.1	20/16	20		50	5	45	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	30		50	3.5	50	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	30		50	3.5	50	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	15		50	3.5	50	1.6
1.2	0.8	0.2	5	1	5	1	0.1	20/16	20		50	2	60	1.6
1.2	0.8	0.2	5	1	5	1	0.1	20/16	20		50	2	60	1.6
1.2	0.8	0.2	5	1	5	1	0.1	20/16	10		50	2	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	25		50	3	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	25		50	3	60	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	10		50	3	60	1.6
1.2	0.8	0.25	8	1	5	1	0.1	20/16	40		50	5	45	1.6
1.2	0.8	0.25	8	1	5	1	0.1	20/16	40		50	5	45	1.6
1.2	0.8	0.25	8	1	5	1	0.1	20/16	20		50	5	45	1.6
1.2	0.8	0.25	5	1	5	1	0.1	20/16	25		50	2.2	60	1.6
1.2	0.8	0.25	5	1	6	1	0.1	20/16	25		50	2.2	60	1.6
1	0.8	0.25	5	1	6	1	0.1	20/16	60		50	3.5	50	1.6
1	0.8	0.25	5	1	6	1	0.1	20/16	40		50	3.5	50	1.6
1	0.8	0.25	5	1	6	1	0.1	20/16	30		50	3.5	50	1.6
1	0.8	0.2	5	1	6	1	0.1	20/16		8	50	4	50	1.6
1	0.8	0.2	5	1	6	1	0.1	20/16		8	50	4	50	1.6
1	0.8	0.2	5	1	6	1	0.1	20/16		8	50	4	50	1.6
1	0.8	0.2	6	1	6	1	0.1	20/16		8	50	5	45	1.6
1	0.8	0.2	6	1	6	1	0.1	20/16		8	50	5	45	1.6
1	0.8	0.2	6	1	6	1	0.1	20/16		8	50	5	45	1.6
1	0.8	0.2	4	1	6	1	0.1	30/25		8	50	3	50	3.7
1	0.8	0.2	4	1	6	1	0.1	30/25		8	50	3	50	3.7
1	0.8	0.2	4	1	6	1	0.1	30/25		8	50	3	50	3.7
1	0.8	0.2	6	1	6	1	0.1	30/25		8	50	4	50	3.7
1	0.8	0.2	6	1	6	1	0.1	30/25		8	50	4	50	3.7
1	0.8	0.2	6	1	6	1	0.1	30/25		8	50	4	50	3.7

See "General Notes" on page E5 - 4 and "Electrical Specifications Notes" on page E5 - 5

TYPE	Part Number				I <sub>T</sub> (1)		V <sub>DRM</sub> & V <sub>RRM</sub>	I <sub>GT</sub> (2) (12)	I <sub>DRM</sub> & I <sub>RRM</sub> (20) (21)		V <sub>TM</sub> (3) (10)
	Isolated	Non-isolated							μAmps		
					Amps		Volts	μAmps	T <sub>C</sub> = 25 °C	T <sub>C</sub> = 110 °C	Volts
	TO-220	TO-202	TO-251 V-Pak	TO-252 D-Pak	I <sub>T(RMS)</sub> MAX	I <sub>T(AV)</sub> MAX			MAX	MAX	
	See "Package Dimensions" section for variations. (11)										
6 A	S2006LS2	S2006FS21	S2006VS2	S2006DS2	6	3.8	200	200	5	250	1.6
	S4006LS2	S4006FS21	S4006VS2	S4006DS2	6	3.8	400	200	5	250	1.6
	S6006LS2	S6006FS21	S6006VS2	S6006DS2	6	3.8	600	200	5	250	1.6
	S2006LS3	S2006FS31	S2006VS3	S2006DS3	6	3.8	200	500	5	250	1.6
	S4006LS3	S4006FS31	S4006VS3	S4006DS3	6	3.8	400	500	5	250	1.6
	S6006LS3	S6006FS31	S6006VS3	S6006DS3	6	3.8	600	500	5	250	1.6
8 A	S2008LS2	S2008FS21	S2008VS2	S2008DS2	8	5.1	200	200	5	250	1.6
	S4008LS2	S4008FS21	S4008VS2	S4008DS2	8	5.1	400	200	5	250	1.6
	S6008LS2	S6008FS21	S6008VS2	S6008DS2	8	5.1	600	200	5	250	1.6
	S2008LS3	S2008FS31	S2008VS3	S2008DS3	8	5.1	200	500	5	250	1.6
	S4008LS3	S4008FS31	S4008VS3	S4008DS3	8	5.1	400	500	5	250	1.6
	S6008LS3	S6008FS31	S6008VS3	S6008DS3	8	5.1	600	500	5	250	1.6
10 A	S2010LS2	S2010FS21	S2010VS2	S2010DS2	10	6.4	200	200	5	250	1.6
	S4010LS2	S4010FS21	S4010VS2	S4010DS2	10	6.4	400	200	5	250	1.6
	S6010LS2	S6010FS21	S6010VS2	S6010DS2	10	6.4	600	200	5	250	1.6
	S2010LS3	S2010FS31	S2010VS3	S2010DS3	10	6.4	200	500	5	250	1.6
	S4010LS3	S4010FS31	S4010VS3	S4010DS3	10	6.4	400	500	5	250	1.6
	S6010LS3	S6010FS31	S6010VS3	S6010DS3	10	6.4	600	500	5	250	1.6

## Specific Test Conditions

$di/dt$  — Maximum rate-of-change of on-state current;  $I_{GT} = 50$  mA pulse width  $\geq 15$   $\mu$ sec with  $\leq 0.1$   $\mu$ s rise time

$dv/dt$  — Critical rate-of-rise of forward off-state voltage

$I^2t$  — RMS surge (non-repetitive) on-state current for period of 8.3 ms for fusing

$I_{DRM}$  and  $I_{RRM}$  — Peak off-state current at  $V_{DRM}$  and  $V_{RRM}$

$I_{GT}$  — DC gate trigger current  $V_D = 6$  V dc;  $R_L = 100 \Omega$

$I_{GM}$  — Peak gate current

$I_H$  — DC holding current; initial on-state current = 20 mA

$I_T$  — Maximum on-state current

$I_{TSM}$  — Peak one-cycle forward surge current

$P_{G(AV)}$  — Average gate power dissipation

$P_{GM}$  — Peak gate power dissipation

$t_{gt}$  — Gate controlled turn-on time gate pulse = 10 mA; minimum width = 15  $\mu$ S with rise time  $\leq 0.1$   $\mu$ s

$t_q$  — Circuit commutated turn-off time

$V_{DRM}$  and  $V_{RRM}$  — Repetitive peak off-state forward and reverse voltage

$V_{GRM}$  — Peak reverse gate voltage

$V_{GT}$  — DC gate trigger voltage;  $V_D = 6$  V dc;  $R_L = 100 \Omega$

$V_{TM}$  — Peak on-state voltage



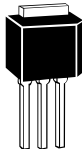


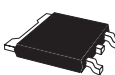
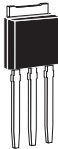
## General Notes

- Teccor 2N5064 and 2N6565 Series devices conform to all JEDEC registered data. See specifications table on pages E5 - 2 and E5 - 3.
- The case lead temperature ( $T_C$  or  $T_L$ ) is measured as shown on dimensional outline drawings in the "Package Dimensions" section of this catalog.
- All measurements (except  $I_{GT}$ ) are made with an external resistor  $R_{GK} = 1$  k $\Omega$  unless otherwise noted.
- All measurements are made at 60 Hz with a resistive load at an ambient temperature of  $+25^\circ C$  unless otherwise specified.
- Operating temperature ( $T_J$ ) is  $-65^\circ C$  to  $+110^\circ C$  for EC Series devices,  $-65^\circ C$  to  $+125^\circ C$  for 2N Series devices,  $-40^\circ C$  to  $+125^\circ C$  for "TCR" Series, and  $-40^\circ C$  to  $+110^\circ C$  for all others.
- Storage temperature range ( $T_S$ ) is  $-65^\circ C$  to  $+150^\circ C$  for TO-92 devices,  $-40^\circ C$  to  $+150^\circ C$  for TO-202 and Compak devices, and  $-40^\circ C$  to  $+125^\circ C$  for all others.
- Lead solder temperature is a maximum of  $+230^\circ C$  for 10 seconds maximum  $\geq 1/16"$  (1.59 mm) from case.

$V_{GT}$			$I_H$	$I_{GM}$	$V_{GRM}$	$P_{GM}$	$P_{G(AV)}$	$I_{TSM}$	$dv/dt$	$di/dt$	$t_{gt}$	$t_q$	$I^2t$
(4) (12) (22)			(5) (19)	(17)		(17)		(6) (13)			(8)	(9)	
Volts									Volts/ $\mu$ Sec				
$T_C = -40^\circ C$	$T_C = 25^\circ C$	$T_C = 110^\circ C$	mAmps	Amps	Volts	Watts	Watts	Amps	$T_C = 110^\circ C$	Amps/ $\mu$ Sec	$\mu$ Sec	$\mu$ Sec	Amps <sup>2</sup> Sec
MAX			MAX		MIN			60/50 Hz	TYP		TYP	MAX	
1	0.8	0.25	6	1	6	1	0.1	100/83	10	100	4	50	41
1	0.8	0.25	6	1	6	1	0.1	100/83	8	100	4	50	41
1	0.8	0.25	6	1	6	1	0.1	100/83	8	100	4	50	41
1	0.8	0.25	8	1	6	1	0.1	100/83	10	100	5	45	41
1	0.8	0.25	8	1	6	1	0.1	100/83	8	100	5	45	41
1	0.8	0.25	8	1	6	1	0.1	100/83	8	100	5	45	41
1	0.8	0.25	6	1	6	1	0.1	100/83	10	100	4	50	41
1	0.8	0.25	6	1	6	1	0.1	100/83	8	100	4	50	41
1	0.8	0.25	6	1	6	1	0.1	100/83	8	100	4	50	41
1	0.8	0.25	8	1	6	1	0.1	100/83	10	100	5	45	41
1	0.8	0.25	8	1	6	1	0.1	100/83	8	100	5	45	41
1	0.8	0.25	8	1	6	1	0.1	100/83	8	100	5	45	41
1	0.8	0.25	6	1	6	1	0.1	100/83	10	100	4	50	41
1	0.8	0.25	6	1	6	1	0.1	100/83	8	100	4	50	41
1	0.8	0.25	6	1	6	1	0.1	100/83	8	100	4	50	41
1	0.8	0.25	8	1	6	1	0.1	100/83	10	100	5	45	41
1	0.8	0.25	8	1	6	1	0.1	100/83	8	100	5	45	41
1	0.8	0.25	8	1	6	1	0.1	100/83	8	100	5	45	41

## Electrical Specifications Notes

- (1) See Figure E5.1 through Figure E5.9 for current ratings at specified operating temperatures.
- (2) See Figure E5.10 for  $I_{GT}$  versus  $T_C$  or  $T_L$ .
- (3) See Figure E5.11 for instantaneous on-state current ( $I_T$ ) versus on-state voltage ( $V_T$ ) TYP.
- (4) See Figure E5.12 for  $V_{GT}$  versus  $T_C$  or  $T_L$ .
- (5) See Figure E5.13 for  $I_H$  versus  $T_C$  or  $T_L$ .
- (6) For more than one full cycle, see Figure E5.14.
- (7) 0.8 A to 4 A devices also have a pulse peak forward current on-state rating (repetitive) of 75 A. This rating applies for operation at 60 Hz, 75 °C maximum tab (or anode) lead temperature, switching from 80 V peak, sinusoidal current pulse width of 10  $\mu$ s minimum, 15  $\mu$ s maximum. See Figure E5.20 and Figure E5.21.
- (8) See Figure E5.15 for  $t_{gt}$  versus  $I_{GT}$ .
- (9) Test conditions as follows:
  - $T_C$  or  $T_L \leq 80^\circ C$ , rectangular current waveform
  - Rate-of-rise of current  $\leq 10$  A/ $\mu$ s
  - Rate-of-reversal of current  $\leq 5$  A/ $\mu$ s
  - $I_{TM} = 1$  A (50  $\mu$ s pulse), Repetition Rate = 60 pps
  - $V_{RRM} = \text{Rated}$
  - $V_R = 15$  V minimum,  $V_{DRM} = \text{Rated}$
  - Rate-of-rise reapplied forward blocking voltage = 5 V/ $\mu$ s
  - Gate Bias = 0 V, 100  $\Omega$  (during turn-off time interval)
- (10) Test condition is maximum rated RMS current except TO-92 devices are 1.2  $A_{PK}$ ; T106/T107 devices are 4  $A_{PK}$ .
- (11) See package outlines for lead form configurations. When ordering special lead forming, add type number as suffix to part number.
- (12)  $V_D = 6$  V dc,  $R_L = 100 \Omega$  (See Figure E5.19 for simple test circuit for measuring gate trigger voltage and gate trigger current.)
- (13) See Figure E5.1 through Figure E5.9 for maximum allowable case temperature at maximum rated current.
- (14)  $I_{GT} = 500 \mu A$  maximum at  $T_C = -40^\circ C$  for T106 devices
- (15)  $I_H = 10$  mA maximum at  $T_C = -65^\circ C$  for 2N5064 Series and 2N6565 Series devices
- (16)  $I_H = 6$  mA maximum at  $T_C = -40^\circ C$  for T106 devices
- (17) Pulse Width  $\leq 10 \mu$ s
- (18)  $I_{GT} = 350 \mu A$  maximum at  $T_C = -65^\circ C$  for 2N5064 Series and 2N6565 Series devices
- (19) Latching current can be higher than 20 mA for higher  $I_{GT}$  types. Also, latching current can be much higher at  $-40^\circ C$ . See Figure E5.18.
- (20)  $T_C$  or  $T_L = T_J$  for test conditions in off state
- (21)  $I_{DRM}$  and  $I_{RRM} = 50 \mu A$  for 2N5064 and 100  $\mu A$  for 2N6565 at 125 °C
- (22) TO-92 devices specified at  $-65^\circ C$  instead of  $-40^\circ C$
- (23)  $T_C = 110^\circ C$

Thermal Resistance (Steady State) $R_{\theta JC}$ [ $R_{\theta JA}$ ] °C/W (TYPICAL)							
Package Code	E	L	F2	F	C	D	V
Type	 TO-92	 TO-220	 TO-202 Type 2, 4, & 41	 TO-202 Type 1 & 3	 Compak	 TO-252 D-Pak	 TO-251 V-Pak
0.8 A	75 [160]				60*		
1.5 A	50 [160]						
4.0 A			10 [100]	6.2 [80]		3.0	3.8 [85]
6.0 A		4.0 [65]		4.3		1.8	2.4
8.0 A		3.4		3.9		1.5	2.1
10.0 A		3.0		3.4		1.45	1.72

\*Mounted on 1 cm<sup>2</sup> copper foil surface; two-ounce copper foil

## Electrical Isolation

Teccor's isolated sensitive SCRs will withstand a minimum high potential test of 2500 V ac rms from leads to mounting tab over the device's operating temperature range. The following table shows other standard and optional isolation ratings.

Electrical Isolation * from Leads to Mounting Tab	
V AC RMS	TO-220
2500	Standard
4000	Optional **

\*UL Recognized File #E71639

\*\*For 4000 V isolation, use "V" suffix in part number.

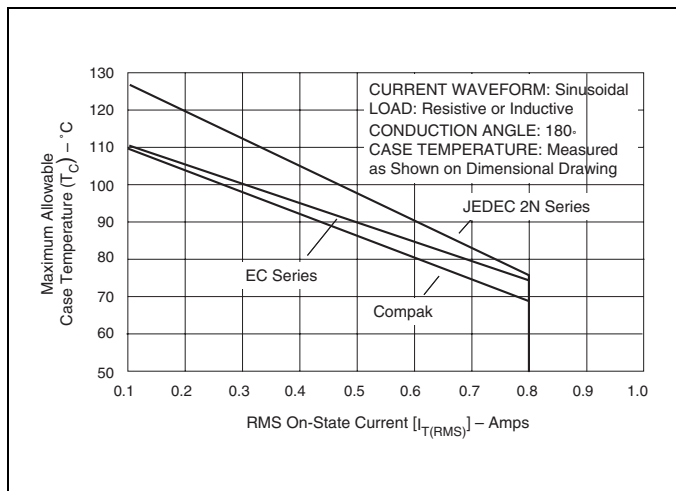


Figure E5.1 Maximum Allowable Case Temperature versus RMS On-state Current

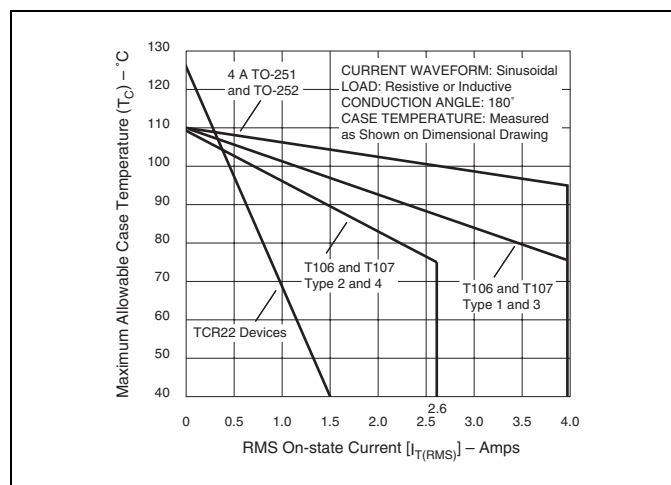


Figure E5.2 Maximum Allowable Case Temperature versus RMS On-state Current

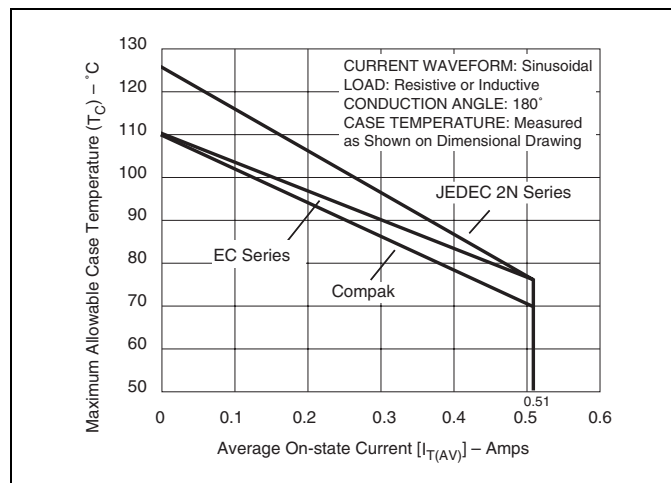


Figure E5.3 Maximum Allowable Case Temperature versus Average On-state Current

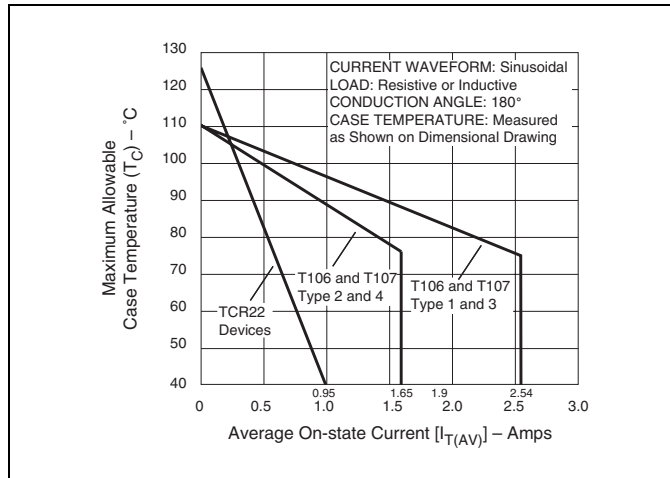


Figure E5.4 Maximum Allowable Case Temperature versus Average On-state Current

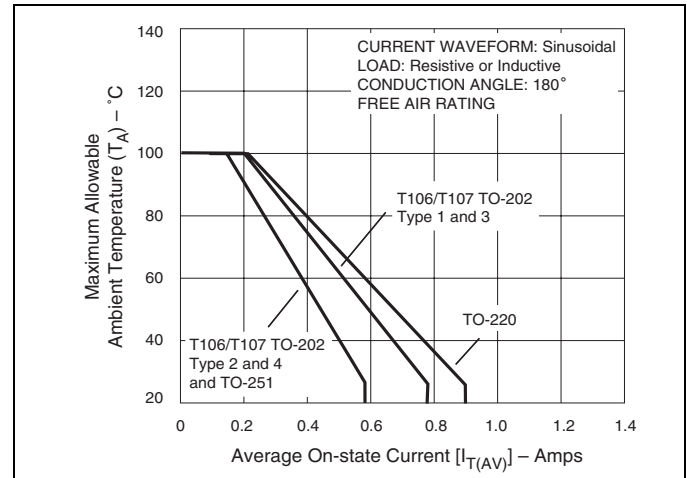


Figure E5.7 Maximum Allowable Ambient Temperature versus Average On-state Current

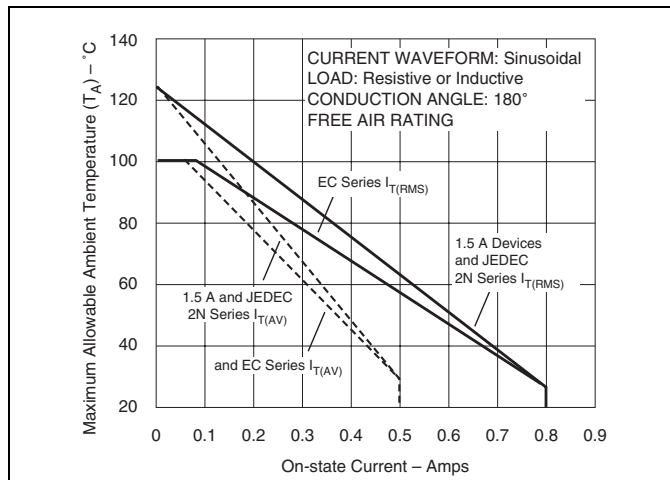


Figure E5.5 Maximum Allowable Ambient Temperature versus On-state Current

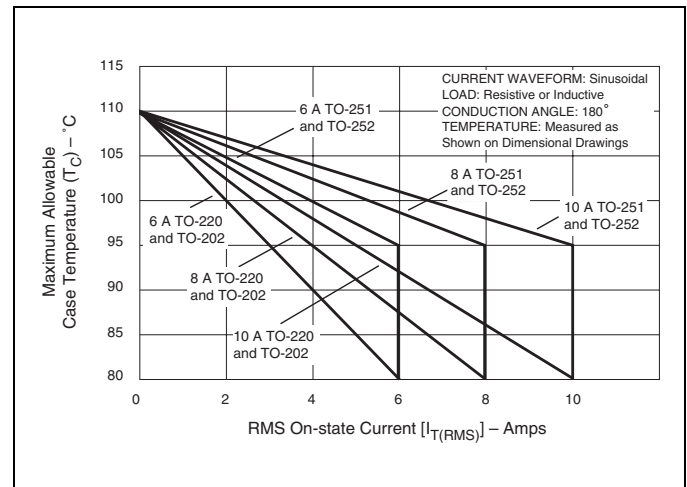


Figure E5.8 Maximum Allowable Case Temperature versus RMS On-state Current

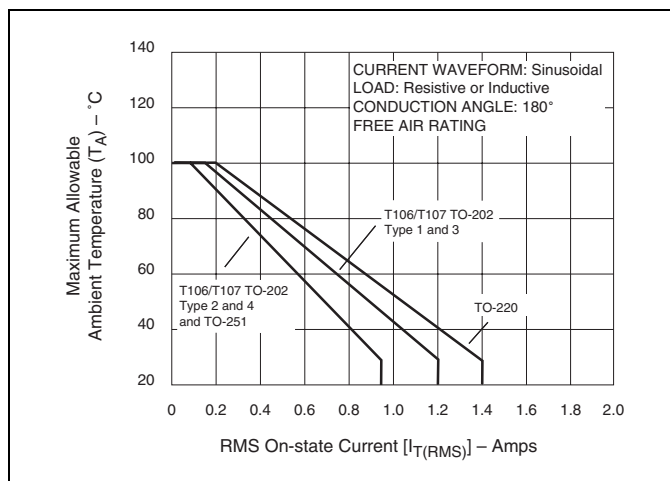


Figure E5.6 Maximum Allowable Ambient Temperature versus RMS On-state Current

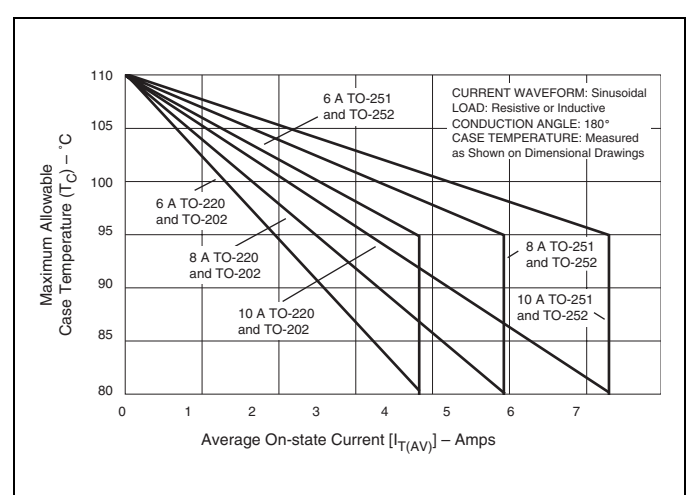


Figure E5.9 Maximum Allowable Case Temperature versus Average On-state Current

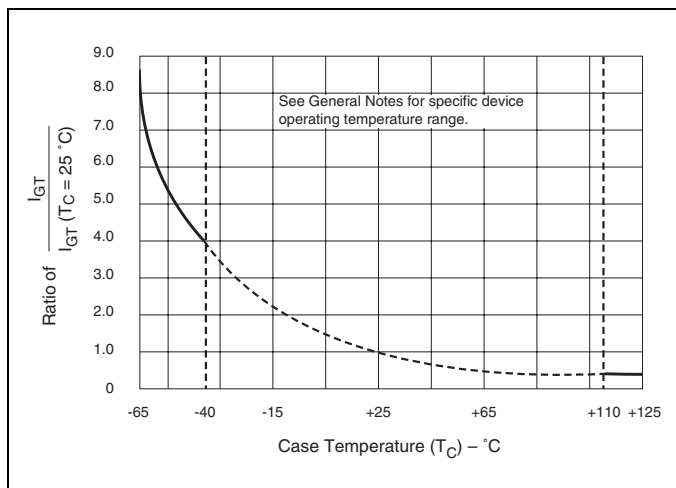


Figure E5.10 Normalized DC Gate-Trigger Current versus Case Temperature

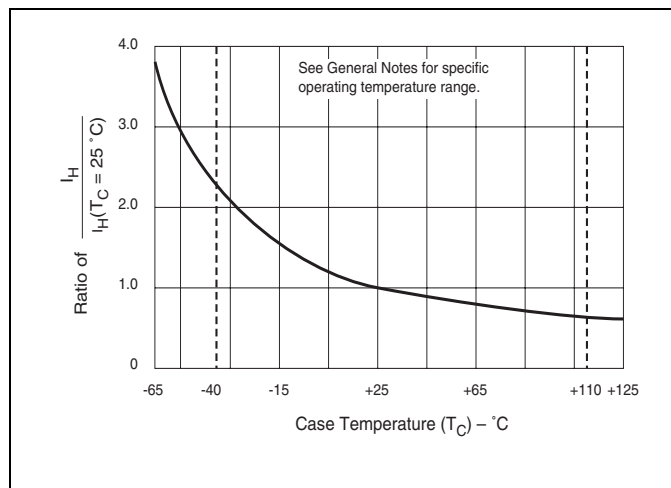


Figure E5.13 Normalized DC Holding Current versus Case Temperature

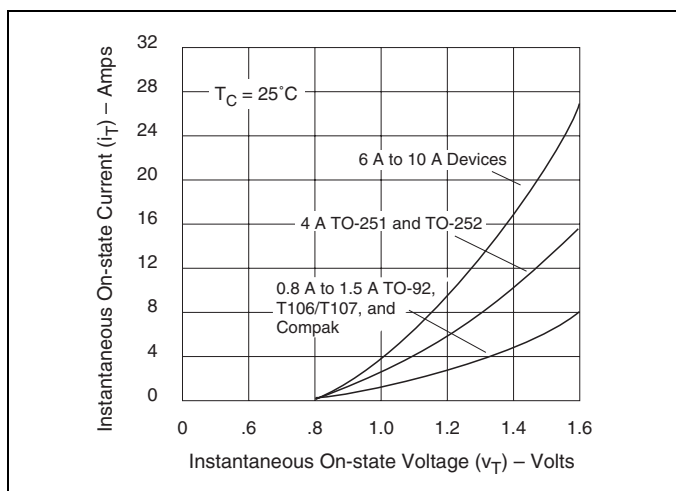


Figure E5.11 Instantaneous On-state Current versus On-state Voltage (Typical)

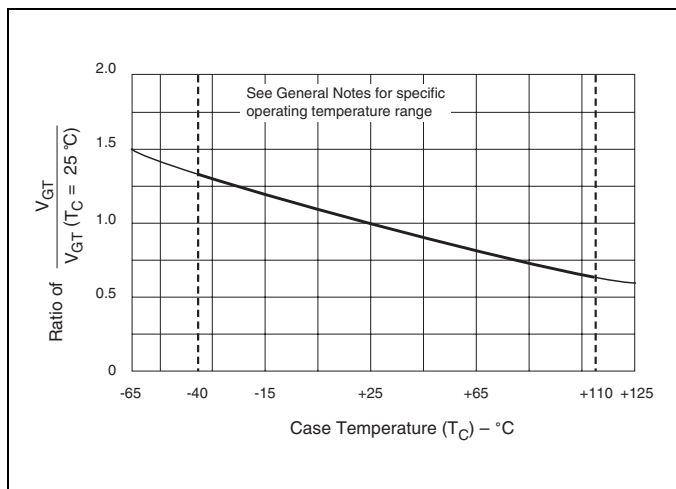


Figure E5.12 Normalized DC Gate-Trigger Voltage versus Case Temperature



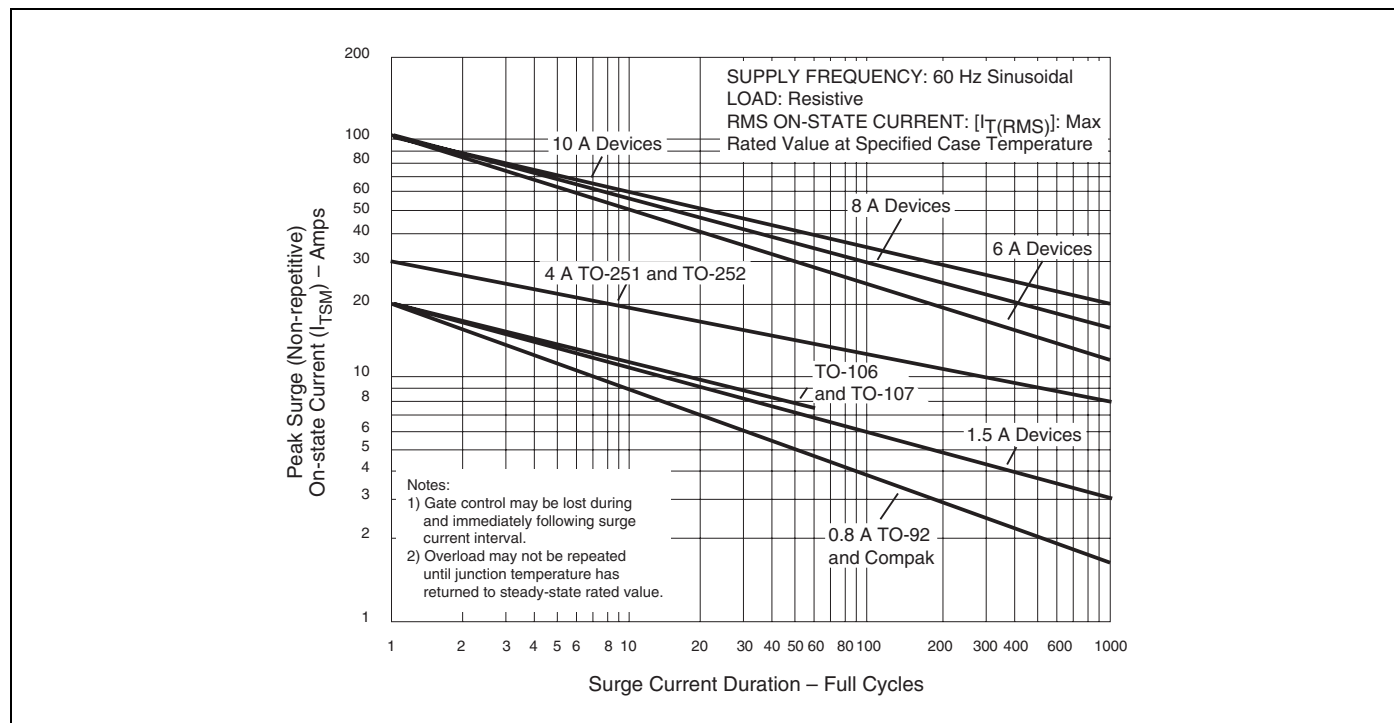


Figure E5.14 Peak Surge On-state Current versus Surge Current Duration

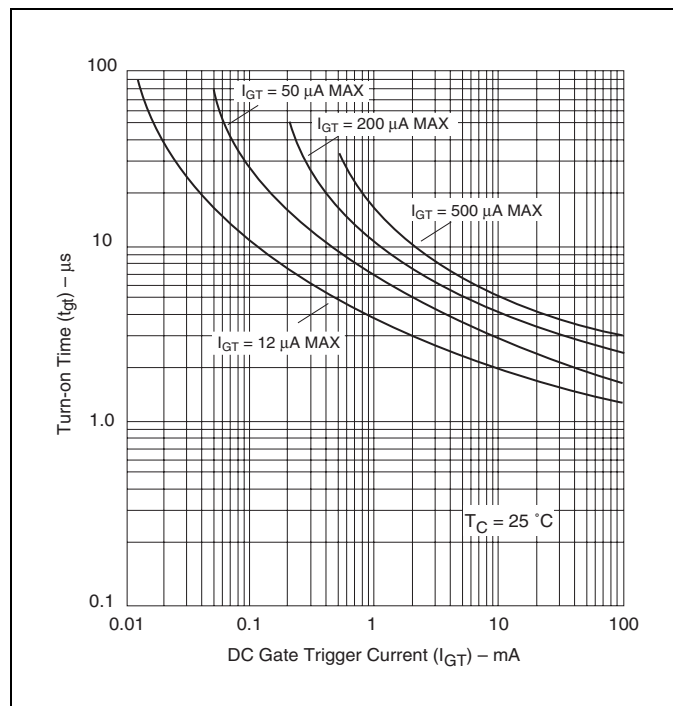


Figure E5.15 Typical Turn-on Time versus Gate Trigger Current

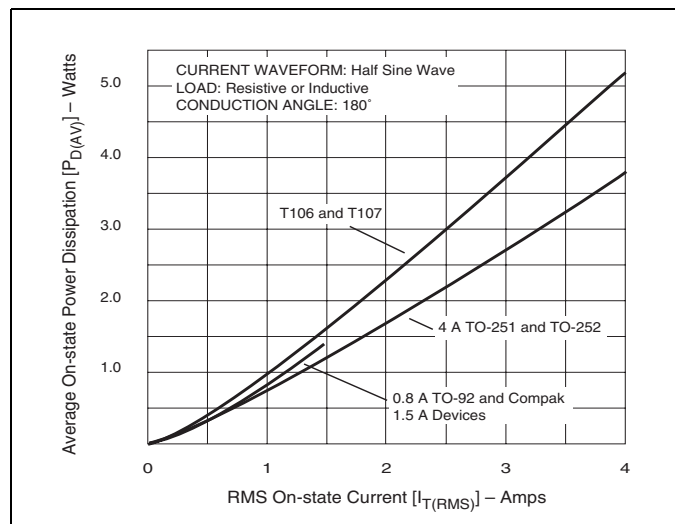


Figure E5.16 Power Dissipation (Typical) versus RMS On-state Current

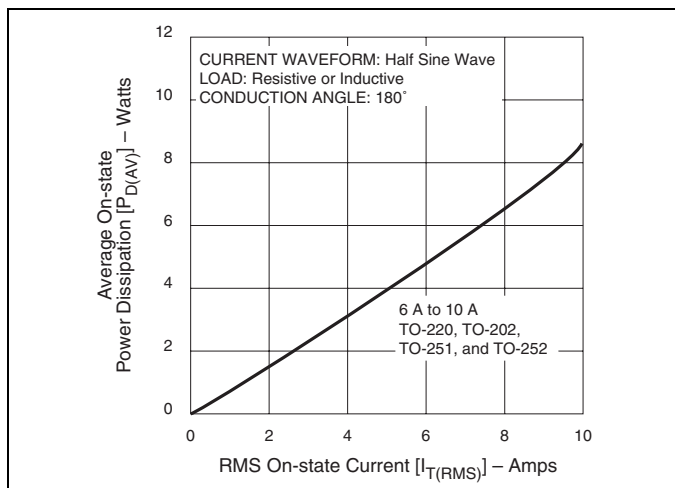


Figure E5.17 Power Dissipation (Typical) versus RMS On-state Current

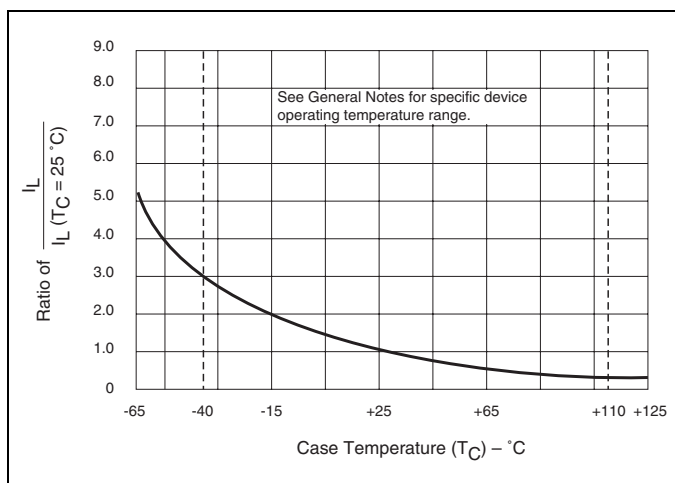


Figure E5.18 Normalized DC Latching Current versus Case Temperature

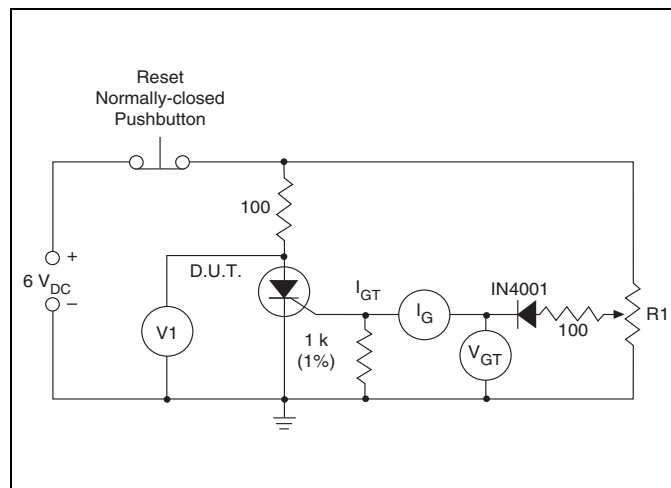


Figure E5.19 Simple Test Circuit for Gate Trigger Voltage and Current Measurement

Note: V1 — 0 V to 10 V dc meter

V<sub>GT</sub> — 0 V to 1 V dc meter

I<sub>G</sub> — 0 mA to 1 mA dc milliammeter

R1 — 1 k potentiometer

To measure gate trigger voltage and current, raise gate voltage (V<sub>GT</sub>) until meter reading V1 drops from 6 V to 1 V. Gate trigger voltage is the reading on V<sub>GT</sub> just prior to V1 dropping. Gate trigger current I<sub>GT</sub> can be computed from the relationship

$$I_{GT} = I_G - \frac{V_{GT}}{1000} \text{ Amps}$$

where I<sub>G</sub> is reading (in amperes) on meter just prior to V1 dropping.

Note: I<sub>GT</sub> may turn out to be a negative quantity (trigger current flows out from gate lead).

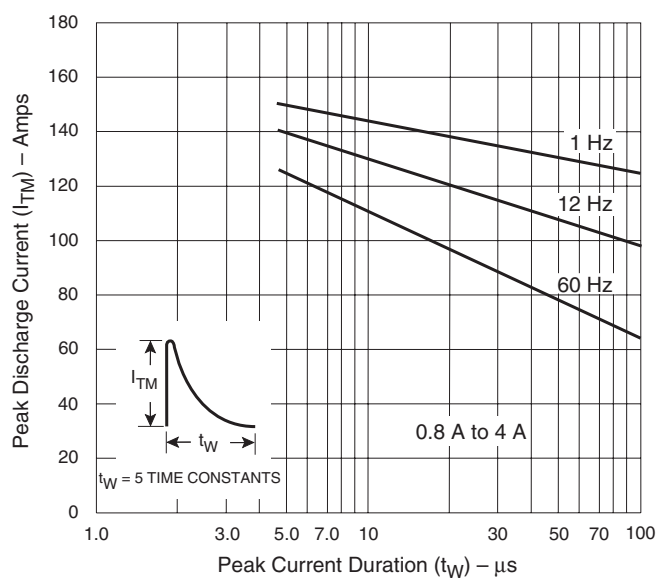


Figure E5.20 Peak Repetitive Capacitor Discharge Current

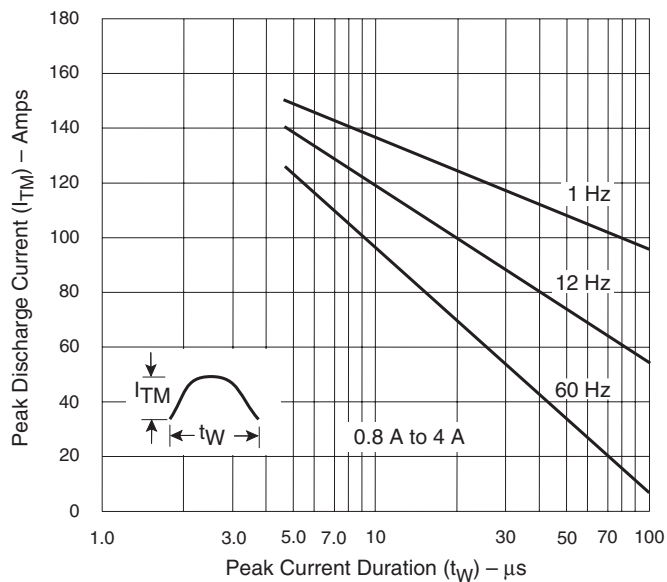


Figure E5.21 Peak Repetitive Sinusoidal Curve

## Notes

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